

--	--	--	--	--	--	--	--	--	--



# INSTITUTE OF AERONAUTICAL ENGINEERING

(Autonomous)

B.Tech IV Semester End Examinations (Regular / Supplementary) - May, 2019

Regulation: IARE – R16

## PULSE AND DIGITAL CIRCUITS

Time: 3 Hours

(ECE)

Max Marks: 70

Answer ONE Question from each Unit

All Questions Carry Equal Marks

All parts of the question must be answered in one place only

### UNIT – I

1. (a) Deduce an expression for the percentage tilt of the output of a high-pass RC circuit with large time constant excited by a symmetrical square wave with zero average value. [7M]
- (b) For the circuit shown in Figure 1 an input voltage  $V_i$  varies linearly from 0 to 150V. Sketch the output waveform  $V_o$  to the same time scale. Assume ideal diodes. [7M]

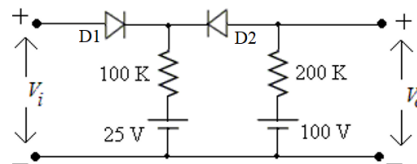


Figure 1

2. (a) Explain the operation of a biased negative clamper with neat sketch. [7M]
- (b) Design a clipping circuit with ideal components, which can give the following waveform shown in Figure 2 for a sinusoidal input. Assume necessary data. [7M]

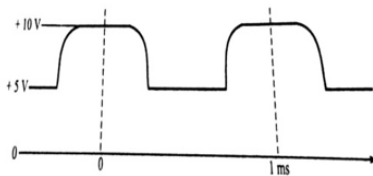


Figure 2

### UNIT – II

3. (a) Identify and apply appropriate multi-vibrating technique to convert sinusoidal signal to square signal, using two transistors. [7M]
- (b) Determine the frequency of oscillations and duty cycle for an astable multivibrator with  $R_1 = 15 \text{ k}\Omega$ ,  $R_2 = 10 \text{ k}\Omega$ ,  $C_1 = 0.01 \text{ }\mu\text{F}$  and  $C_2 = 0.015 \text{ }\mu\text{F}$ . [7M]

4. (a) What do you understand by hysteresis? What is hysteresis voltage? Explain how hysteresis can be eliminated in a Schmitt trigger. [7M]
- (b) The self-biased bistable multivibrator uses silicon transistors with  $h_{FE(min)} = 20$ . The junction voltages and  $I_{CBO}$  may be neglected. Design the circuit subject to the condition  $V_{CC} = 18\text{ V}$ ,  $R_1 = R_2$ ,  $I_{C(max)} = 10\text{ mA}$ . The base current of ON transistor is twice the minimum base current, and  $V_{BE}$  of the off transistor is equal to  $-1\text{ V}$ . [7M]

### UNIT – III

5. (a) Define the terms slope error, displacement error and transmission error. How are they related for an exponential sweep circuit? Define the relation between them [7M]
- (b) Calculate sweep interval of a UJT sweep circuit for following specifications.  $\eta = 0.68$ ,  $V_{BB} = 12\text{V}$ ,  $V_v = 0.8\text{V}$ ,  $V_p = 6\text{V}$ . [7M]
6. (a) Demonstrate the working of two-diode sampling gate with necessary diagrams and equations. [7M]
- (b) A transistor bootstrap ramp generator is to produce a  $15\text{ V}$ ,  $5\text{ ms}$  output to a  $2\text{ k}$  load resistor. The ramp is to be linear within  $2\%$ . Design a suitable circuit using  $V_{CC} = 22\text{ V}$ ,  $-V_{EE} = -22\text{ V}$  and transistor with  $h_{fe(min)} = 25$ . The input pulse has an amplitude of  $-5\text{ V}$ , pulse width =  $5\text{ ms}$  and space width =  $2.5\text{ ms}$ . [7M]

### UNIT – IV

7. (a) What is the need of synchronization and explain the method of synchronization of a sinusoidal oscillator with pulses. [7M]
- (b) Frequency division of 6:1 is obtained with an astable multivibrator, negative pulses are applied simultaneously to both bases of the n-p-n transistors. The OFF time of  $Q_1(V_1)$  is twice that of  $Q_2(V_2)$ . Sketch the wave shapes at base terminals. [7M]
8. (a) What do you mean by relaxation circuit. Explain the principle of operation of sweep generator using UJT with neat sketches. Explain the concept of stability of relaxation devices. [7M]
- (b) Design a relaxation oscillator to have  $3\text{KHz}$  output frequency using UJT and a  $20\text{V}$  supply. Calculate the sweep amplitude. The specifications from the data sheet are given as  $\eta=0.7$ ,  $I_p=2\mu\text{A}$ ,  $I_v=1\mu\text{A}$ , and  $V_{BEsat}=3\text{V}$ . [7M]

### UNIT – V

9. (a) Describe in detail the working of transistor inverter logic using circuit diagram. Discuss the function of two-input ECL OR/NOR gate with neat diagram. [7M]
- (b) Design a transistor inverter circuit (NOT gate) with the following specifications:  $V_{CC} = V_{BB} = 10\text{V}$ ,  $I_{Csat} = 10\text{mA}$ ,  $h_{fe(min)} = 30$ . The input is varying between  $0$  and  $10\text{V}$ . Assume typical junction voltages of npn silicon transistor [7M]
10. (a) Draw and explain the circuit of two-input TTL NAND with totem pole output. Implement NAND gate using CMOS logic [7M]
- (b) The two-input diode AND circuit shown uses diodes with  $R_f = 200\Omega$ ,  $R_r = 1\text{M}\Omega$  and the currents in  $D_1$  and  $D_2$  are each  $2\text{ mA}$  &  $6\text{ mA}$  respectively. Then calculate the output voltage when one input diode is cut-off. [7M]